

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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DATASHEET

4 PIN SOP PHOTOTRANSISTOR PHOTOCOUPLER EL357N-G Series



Features:

- Halogens free
- Current transfer ratio (CTR: 50~600% at I_F =5mA, V_{CE} =5V)
- High isolation voltage between input and output (Viso=3750 V rms)
- · Compact 4 Pin SOP with a 2.0 mm profile
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CSA approved (No. 1408633)

Description

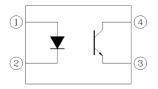
The EL357N-G series contains an infrared emitting diode, optically coupled to a phototransistor detector.

The devices in a 4-pin small outline SMD package.

Applications

- DC-DC Converters
- Programmable controllers
- Telecommunication equipments
- Signal transmission between circuits of different potentials and impedances

Schematic



Pin Configuration

- 1. Anode
- 2. Cathode
- 3. Emitter
- 4. Collector



Absolute Maximum Ratings (Ta=25℃)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I _F	50	mA
	Peak forward current (1us, pulse)	I _{FP}	1	А
	Reverse voltage	V_{R}	6	V
	Power dissipation		70	mW
	Derating factor (about Ta=100 °C)	P _D —	2.9	mW/° C
Output	Power dissipation	_	150	mW
	Derating factor (above $T_a = 70^{\circ}C$)	P _C —	3.7	mW/℃
	Collector current	I _C	50	mA
	Collector-Emitter voltage	V_{CEO}	80	V
	Emitter-Collector voltage	V _{ECO}	7	V
Total Power Dissipation		P _{TOT}	200	mW
Isolation Voltage*1		V _{ISO}	3750	V rms
Operating temperature		T _{OPR}	-55 ~ +110	∞
Storage t	Storage temperature		-55 ~ +125	∞
Soldering	g Temperature*2	T _{SOL}	260	∞

Notes:

^{*1} AC for 1 minute, R.H.= $40 \sim 60\%$ R.H. In this test, pins 1, 2 are shorted together, and pins 3, 4 are shorted together.

^{*2} For 10 seconds



Electro-Optical Characteristics (Ta=25℃ unless specified otherwise)

Input

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	V_{F}	-	1.2	1.4	V	I _F = 20mA
Reverse current	I _R	-	-	10	μΑ	$V_R = 4V$
Input capacitance	C _{in}	-	30	250	pF	V = 0, f = 1kHz

Output

Parameter	Symbol	Min	Тур.	Max.	Unit	Condition
Collector-Emitter dark current	I _{CEO}	-	-	100	nA	$V_{CE} = 20V, I_F = 0mA$
Collector-Emitter breakdown voltage	BV_CEO	80	-	-	V	I _C = 0.1mA
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	I _E = 0.01mA

Transfer Characteristics (T_a=25 °C unless specified otherwise)

Parameter		Symbol	Min	Тур.	Max.	Unit	Condition
Current Transfer ratio	EL357N		50	-	600	%	$I_F = 5mA$, $V_{CE} = 5V$
	EL357NA	_	80	-	160		
	EL357NB		130	-	260		
	EL357NC	CTR	200	-	400		
	EL357ND	-	300	-	600		
	EL357NE		100	-	200		
	EL357NF	_	150	-	300		
Collector-Emitter saturation voltage		$V_{\text{CE(sat)}}$	-	0.1	0.2	V	$I_F = 20 \text{mA}$, $I_C = 1 \text{mA}$
Isolation resistance		R _{IO}	5×10 ¹⁰	-	-	Ω	V _{IO} = 500Vdc, 40∼60% R.H.
Floating capacitance		C_{IO}	-	0.6	1.0	pF	$V_{IO} = 0$, $f = 1MHz$
Rise time	Rise time		-	3	18		$V_{CE} = 2V, I_{C} = 2mA,$
Fall time	Fall time		-	4	18	μs	$R_L = 100\Omega$

^{*} Typical values at T_a = 25°C



Typical Electro-Optical Characteristics Curves

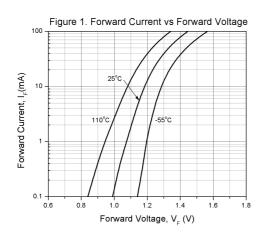


Figure 2. Normalized Collector Current vs
Forward Current

V_{cE}=10V
V_{cE}=5V

V_{cE}=0.4V

T_A=25°C
Normalized to I_F=5mA₁V_{CE}=5V

Forward Current, I_E (mA)

Figure 3. Normalized Current Transfer Ratio vs
Forward Current

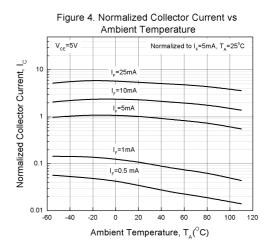
T_A=25°C

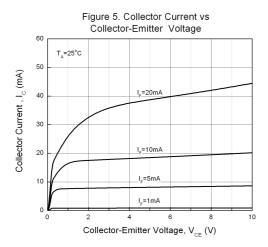
Normalized to I_p=5mA,V_{CE}=5V

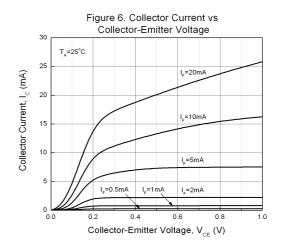
V_{CE}=10V

V_{CE}=0.4V

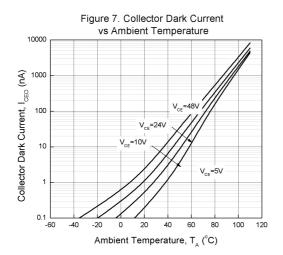
Forward Current, IF (mA)

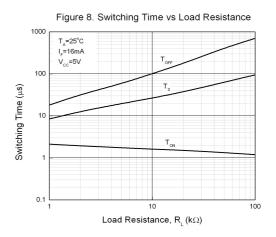


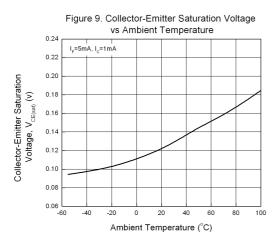


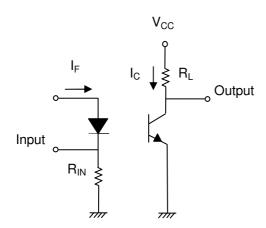












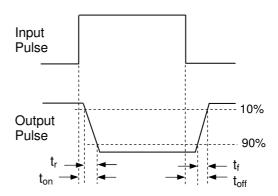


Figure 10. Switching Time Test Circuit & Waveforms



Order Information

Part Number

EL357N(X)(Y)-VG

Note

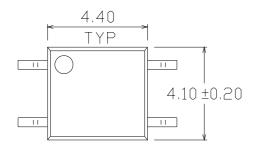
X = CTR Rank (A, B, C, D, E, For none) Y = Tape and reel option (TA, TB, or none).

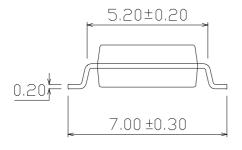
V = VDE (option) G = Halogens free

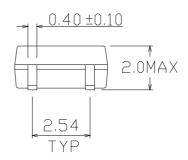
Option	Description	Packing quantity		
None	Standard SMD option	100 units per tube		
-V	Standard SMD option + VDE	100 units per tube		
(TA)	TA Tape & reel option	3000 units per reel		
(TB)	TB Tape & reel option	3000 units per reel		
(TA)-V	TA Tape & reel option + VDE	3000 units per reel		
(TB)-V	TB Tape & reel option + VDE	3000 units per reel		



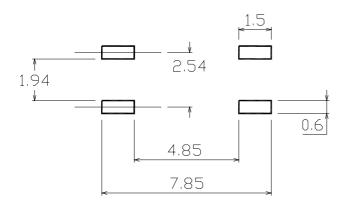
Package Dimension (Dimensions in mm)







Recommended pad layout for surface mount leadform





Device Marking



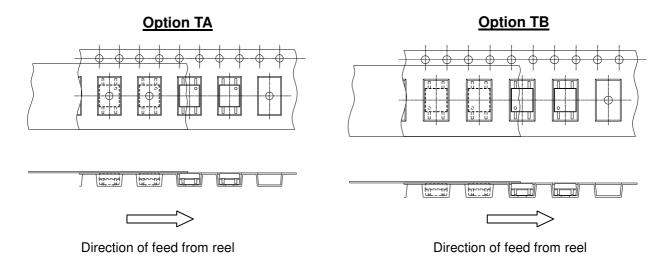
Notes

EL denotes Everlight
357N denotes Device Number
R denotes CTR Rank
Y denotes 1 digit Year code
WW denotes 2 digit Week code

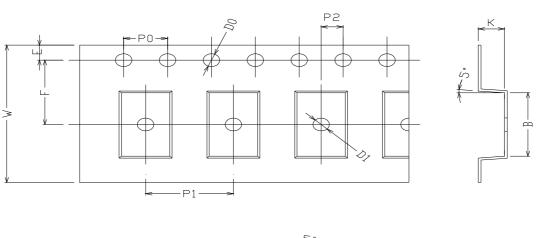
V denotes VDE approved (optional)



Tape & Reel Packing Specifications



Tape dimensions





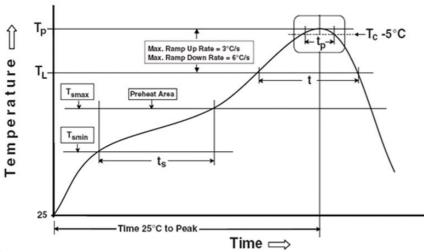
Dimension No.	Α	В	Do	D1	E	F
Dimension (mm)	4.4 ± 0.1	7.4 ± 0.1	1.5 + 0.1/-0	1.5 ± 0.1	1.7 5± 0.1	7.5 ± 0.1
Dimension No.	Ро	P1	P2	t	W	К
Dimension (mm)	4.0 ± 0.15	8.0 ± 0.1	2.0 ± 0.1	0.25 ± 0.03	16.0 ± 0.2	2.4 ± 0.1



Precautions for Use

1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

Preheat

150 ℃ Temperature min (T_{smin}) Temperature max (T_{smax}) 200℃

60-120 seconds Time $(T_{smin} \text{ to } T_{smax}) (t_s)$ Average ramp-up rate $(T_{smax} to T_p)$ 3 °C/second max

Other

217 ℃ Liquidus Temperature (T_L) Time above Liquidus Temperature (t L)

Peak Temperature (T_P)

Time within 5 °C of Actual Peak Temperature: T_P - 5 °C

Ramp- Down Rate from Peak Temperature

Time 25 °C to peak temperature

Reflow times

60-100 sec

260℃

30 s

6°C /second max.

8 minutes max.

3 times



DISCLAIMER

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